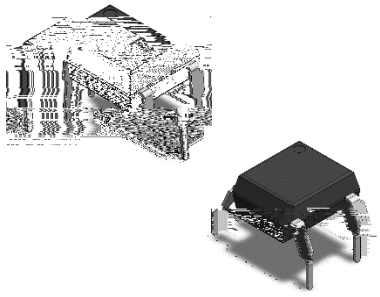
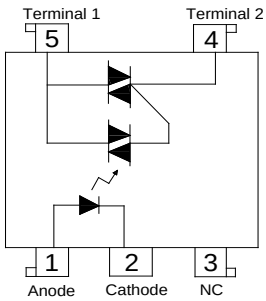
H11BXF Series

Rev.A.1.1

The H11BXF series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a monolithic silicon random-phase photo triac to drive a power triac in a plastic DIP5 package with different lead forming options. The products are widely used in solenoid/valve controls, lighting controls, motor controls, temperature controls, static AC power switches, solid state relays, interfacing microprocessors to 265 V_{AC} peripherals.





High isolation 5000 Vrms
DC input with triac output
Operating temperature range - 40°C to 85 °C
REACH & RoHS compliance
MSL class 2
HBM: H3A; MM: M4
CQC approved
VDE approved
UL approved

(Temperature=25°C)

Parameter			Symbol	Value	Unit
Input	Forward Current		I_F	60	mA
	Peak Forward Current		I_{FP}	1	A
	Reverse Voltage		V_R	6	V
Output	Repetitive peak off-state voltage		V_{DRM}	600	V
	Repetitive peak off-state voltage		V_{RRM}	600	V
	Critical rate of rise of on-state current		dI/dt	70	A/μs
	On-state RMS Current	H11B0F	$I_{T(RMS)}$	0.3	A
		H11B1F		0.6	
	Non repetitive surge peak on-state current (full cycle , t_p=20ms)	H11B0F	I_{TSM}	3	A
		H11B1F		6	
Isolation Voltage			V_{iso}	5000	Vrms

Operating Temperature	T_{opr}	-40~85	
Storage Temperature	T_{stg}	-40~125	
Soldering Temperature	T_{sol}	260	

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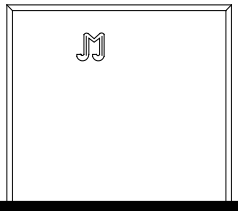


FIG.1: Forward Current vs. Ambient Temperature

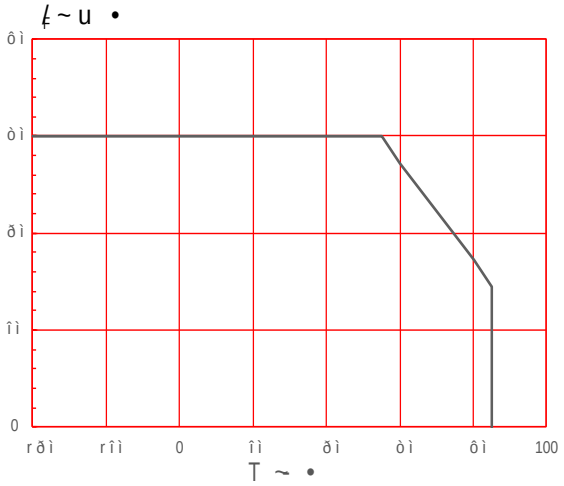
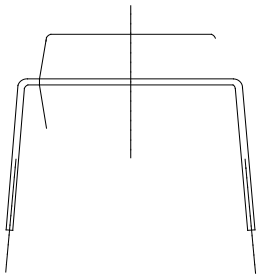


FIG.2: On-state Terminal Current vs. Ambient Temperature

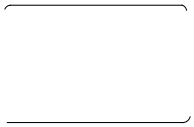
FIG.10: Test Circuits of Turn On Time

FIG.11: Waveforms of Turn On Time

Standard DIP Type:



Option SL Type:



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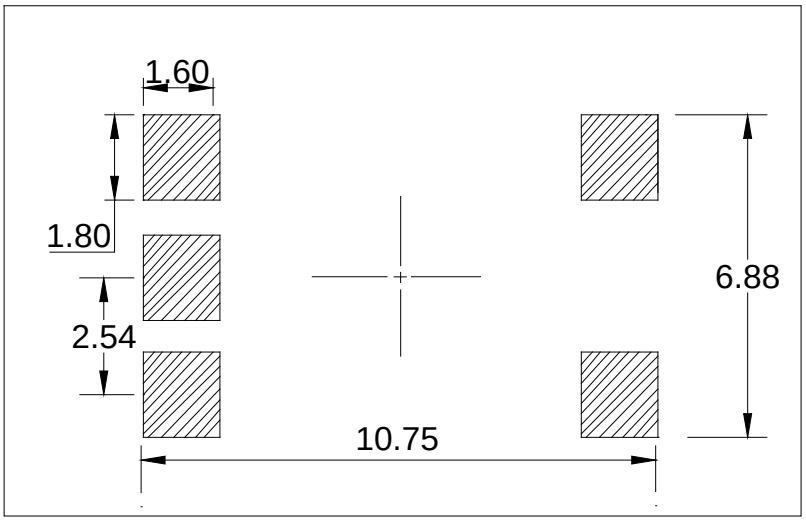
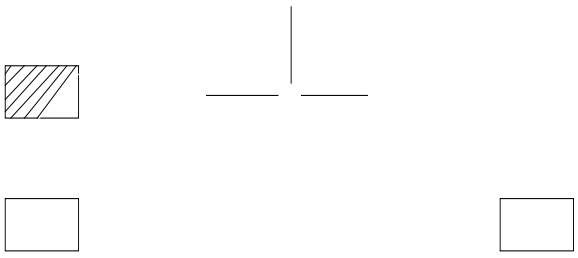
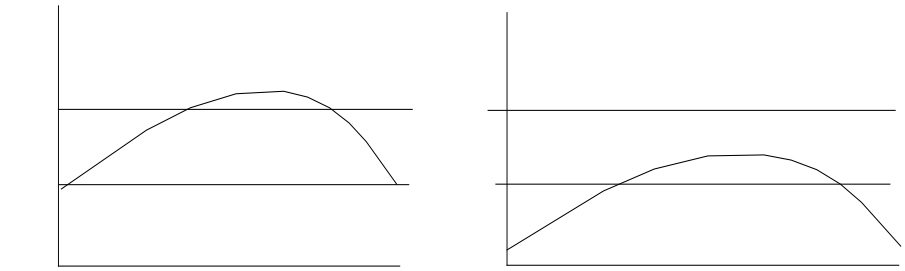
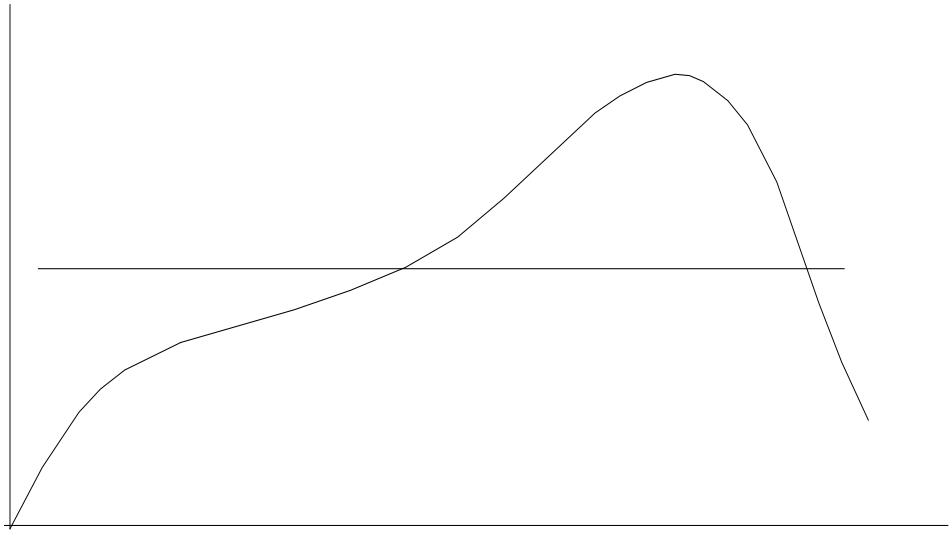


SLM:







H11BXF